

Nch 500V 9A Power MOSFET

V_{DSS}	500V
R _{DS(on)} (Max.)	0.84Ω
I _D	9A
P_D	51W

● Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Gate-source voltage (V_{GSS}) guaranteed to be $\pm 30V$.
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.
- 6) Pb-free lead plating; RoHS compliant

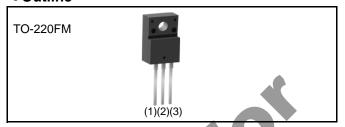
Application

Switching Power Supply

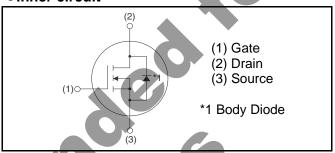
● Absolute maximum ratings(T_a = 25°C)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	500	V
Continuous drain current	I _D *1	±9	А
T _c = 100° C	I _D *1	±4.4	А
Pulsed drain current	I _{D,pulse} *2	±36	А
Gate - Source voltage	V_{GSS}	±30	V
Avalanche energy, single pulse	E _{AS} *3	5.4	mJ
Avalanche energy, repetitive	E _{AR} *4	3.5	mJ
Avalanche current	I _{AR} *3	4.5	А
Power dissipation $(T_c = 25^{\circ}C)$	P_{D}	51	W
Junction temperature	T _j	150	°C
Range of storage temperature	T _{stg}	-55 to +150	°C
Reverse diode dv/dt	dv/dt *5	15	V/ns

Outline



●Inner circuit



Packaging specifications

Tackaging specifications					
	Packaging	Bulk			
	Reel size (mm)	-			
Type	Tape width (mm)	-			
Туре	Basic ordering unit (pcs)	500			
~(2	Taping code	-			
	Marking	R5009FNX			

Absolute maximum ratings

Parameter	Symbol	Conditions	Values	Unit
Drain - Source voltage slope	dv/dt	$V_{DS} = 400V, I_{D} = 9A$ $T_{j} = 125^{\circ}C$	50	V/ns

●Thermal resistance

Parameter	Symbol	Values			Unit
- Farameter	Symbol	Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	R_{thJC}	-	S	2.43	°C/W
Thermal resistance, junction - ambient	R _{thJA}		,	70	°C/W
Soldering temperature, wavesoldering for 10s	T _{sold}		-	265	°C

•Electrical characteristics($T_a = 25$ °C)

Parameter	Symbol	Conditions	j	Values		Unit
r arameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	V _{(BR)DSS}	$V_{GS} = 0V$, $I_D = 1mA$	500	-	-	V
Drain - Source avalanche breakdown voltage	V _{(BR)DS}	$V_{GS} = 0V, I_{D} = 9A$	-	580	1	V
		$V_{DS} = 500V, V_{GS} = 0V$				^
Zero gate voltage drain current	I _{DSS}	$T_j = 25^{\circ}C$	-	1	100	μΑ
		T _j = 125°C	ı	ı	10	mA
Gate - Source leakage current	I _{GSS}	$V_{GS} = \pm 30V, V_{DS} = 0V$	ı	ı	±100	nA
Gate threshold voltage	V _{GS (th)}	$V_{DS} = 10V$, $I_D = 1mA$	2	-	4	V
		$V_{GS} = 10V, I_D = 4.5A$				
Static drain - source on - state resistance	R _{DS(on)} *6	T _j = 25°C	-	0.65	0.84	Ω
2.522		T _j = 125°C	-	1.37	-	
Gate input resistance	R_{G}	f = 1MHz, open drain	-	8.2	-	Ω

●Electrical characteristics(T_a = 25°C)

Parameter	Symbol	Conditions		Values		Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Transconductance	g _{fs} *6	$V_{DS} = 10V, I_{D} = 4.5A$	4.0	5.7	1	S
Input capacitance	C _{iss}	V _{GS} = 0V	-	630	-	
Output capacitance	C _{oss}	V _{DS} = 25V	-	400		pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	25		
Effective output capacitance, energy related	C _{o(er)}	V _{GS} = 0V	-	41.5	-	
Effective output capacitance, time related	$C_{o(tr)}$	$V_{DS} = 0V \text{ to } 400V$	NO.	40.4	-	pF
Turn - on delay time	t _{d(on)} *6	$V_{DD} \simeq 250V$, $V_{GS} = 10V$	J -	24	-	
Rise time	t _r *6	I _D = 4.5A	-	20	-	20
Turn - off delay time	t _{d(off)} *6	$R_L = 55.6\Omega$		50	100	ns
Fall time	t _f *6	$R_G = 10\Omega$		40	80	

●Gate Charge characteristics(T_a = 25°C)

Parameter	Symbol Conditions -		Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	Qg *6	V _{DD} ≃ 250V	ı	18	1	
Gate - Source charge	Q _{gs} *6	I _D = 9A	-	3.5	-	nC
Gate - Drain charge	Q _{gd} *6	V _{GS} = 10V	-	5.5	-	
Gate plateau voltage	V _(plateau)	$V_{DD} \simeq 250V, I_D = 9A$	-	5.8	-	V

^{*1} Limited only by maximum temperature allowed.

^{*2} Pw \leq 10 μ s, Duty cycle \leq 1%

^{*3} L $^{\simeq}$ 500 μ H, V_{DD} = 50V, R_{G} = 25 Ω , starting T_{j} = 25°C

^{*4} L $^{\sim}$ 500 μ H, V_{DD} = 50V, R_G = 25 Ω , starting T_j = 25°C, f = 10kHz

^{*5} Reference measurement circuits Fig.5-1.

^{*6} Pulsed

ullet Body diode electrical characteristics (Source-Drain)(T_a = 25°C)

Parameter	Symbol	vmbol Conditions Values		Values		Unit
r ai ai i letei	Parameter Symbol Conditi		Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	l _S *1	T - 25°C	-	,	9	A
Inverse diode direct current, pulsed	I _{SM} *2	T _c = 25°C	'	-	36	А
Forward voltage	V _{SD} *6	$V_{GS} = 0V, I_S = 9A$	-	-	1.5	V
Reverse recovery time	t _{rr} *6		48	78	108	ns
Reverse recovery charge	Q _{rr} *6	I _S = 9A di/dt = 100A/us		0.2	ı	μС
Peak reverse recovery current	I _{rrm} *6]	5.2	ı	А
Peak rate of fall of reverse recovery current	di _{rr} /dt	T _j = 25°C	-	610	-	A/μs

●Typical Transient Thermal Characteristics

Symbol	Value	Unit	Syı
R _{th1}	0.263		
R_{th2}	0.977	K/W	C
R _{th3}	2.18		C

Symbol	ool Value	
C _{th1}	0.00166	
C _{th2}	0.0191	Ws/K
C_{th3}	0.46	

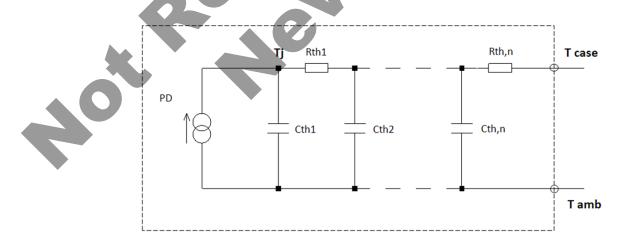
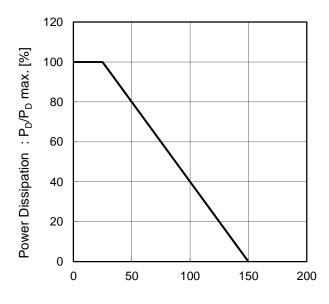
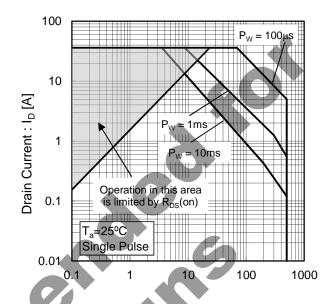


Fig.1 Power Dissipation Derating Curve



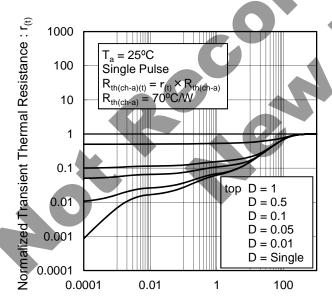
Junction Temperature : Tj [°C]

Fig.2 Maximum Safe Operating Area



Drain - Source Voltage : V_{DS} [V]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



Pulse Width: P_W [s]

Fig.4 Avalanche Current vs Inductive Load

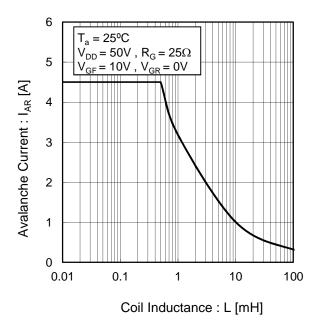
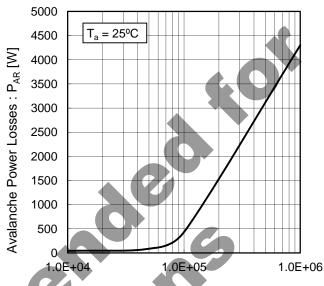
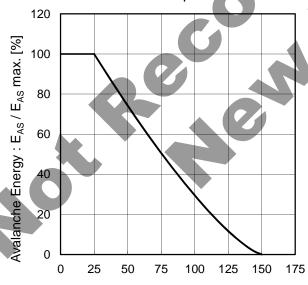


Fig.5 Avalanche Power Losses



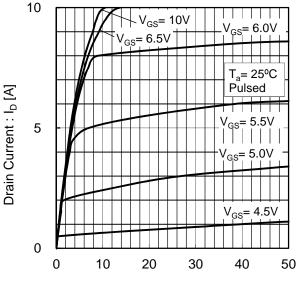
Frequency: f [Hz]

Fig.6 Avalanche Energy Derating Curve vs Junction Temperature



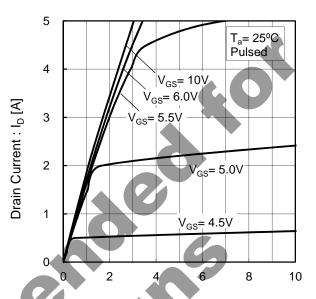
Junction Temperature : T_j [°C]

Fig.7 Typical Output Characteristics(I)



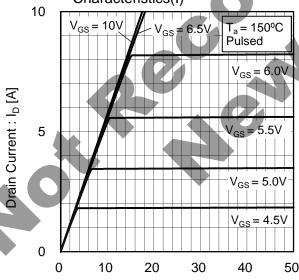
Drain - Source Voltage : V_{DS} [V]

Fig.8 Typical Output Characteristics(II)



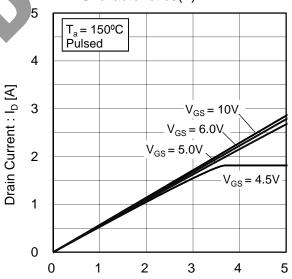
Drain - Source Voltage : V_{DS} [V]

Fig.9 T_j = 150°C Typical Output Characteristics(I)



Drain - Source Voltage : V_{DS} [V]

Fig. 10 T_j = 150°C Typical Output Characteristics(II)



Drain - Source Voltage : V_{DS} [V]

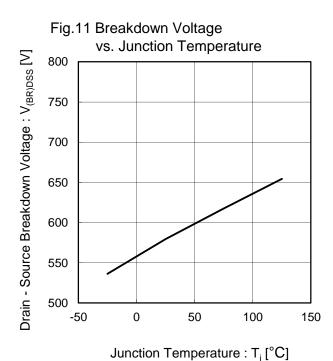
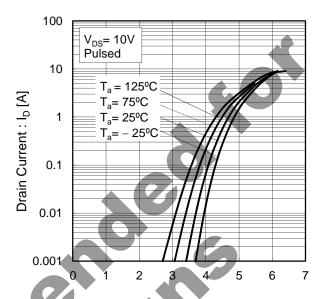


Fig.12 Typical Transfer Characteristics



Gate - Source Voltage : V_{GS} [V]

Fig.13 Gate Threshold Voltage vs. Junction Temperature

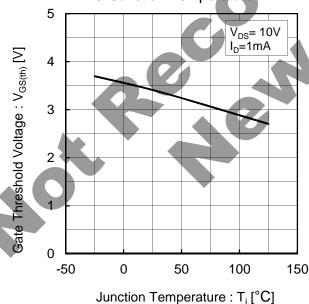


Fig.14 Transconductance vs. Drain Current

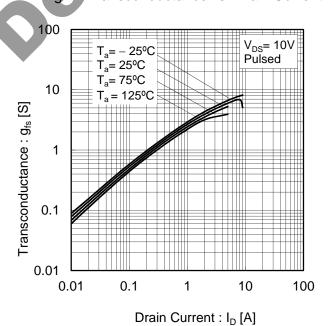
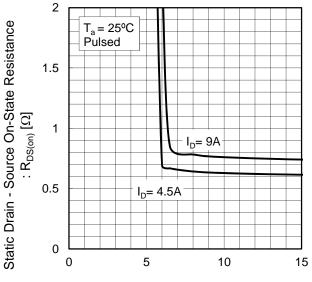
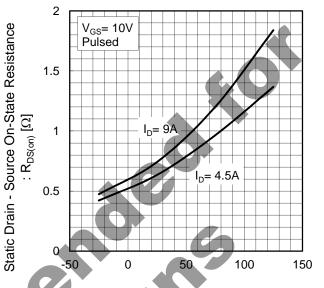


Fig.15 Static Drain - Source On - State Resistance vs. Gate Source Voltage



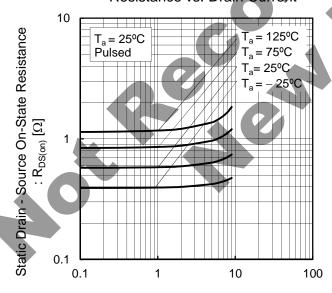
Gate - Source Voltage : V_{GS} [V]

Fig.16 Static Drain - Source On - State Resistance vs. Junction Temperature



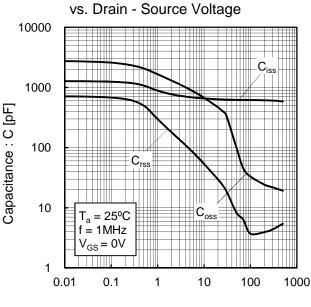
Junction Temperature : T_i [°C]

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current



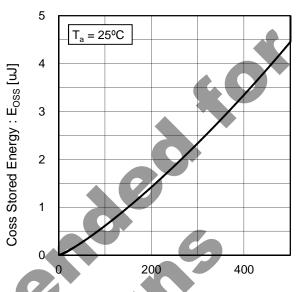
Drain Current : I_D [A]

Fig.18 Typical Capacitance



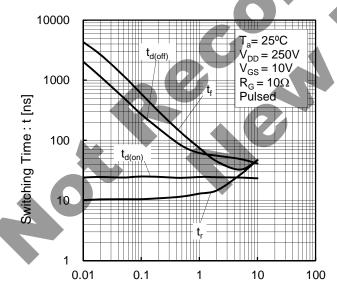
Drain - Source Voltage : V_{DS} [V]

Fig.19 Coss Stored Energy



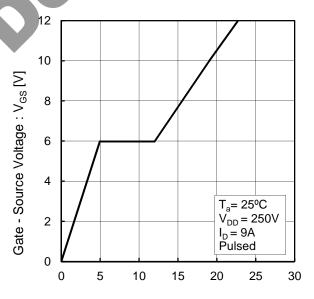
Drain - Source Voltage : V_{DS} [V]

Fig.20 Switching Characteristics



Drain Current : I_D [A]

Fig.21 Dynamic Input Characteristics



Total Gate Charge : Q_g [nC]

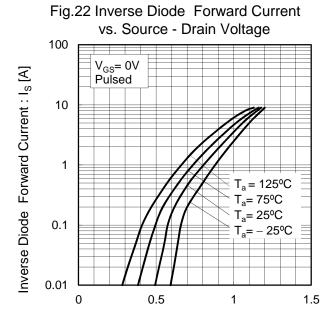


Fig. 23 Reverse Recovery Time
vs. Inverse Diode Forward Current

1000

T_a= 25°C
Pulsed

100

100

100

100

100

100

100

Source - Drain Voltage : V_{SD} [V]

Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

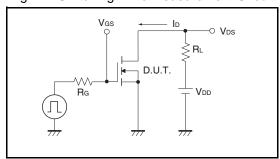


Fig.2-1 Gate Charge Measurement Circuit

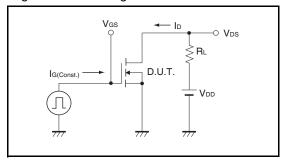


Fig.3-1 Avalanche Measurement Circuit

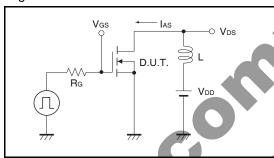


Fig.4-1 dv/dt Measurement Circuit

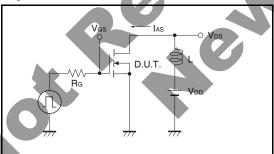


Fig.5-1 di/dt Measurement Circuit

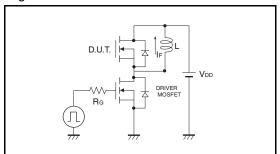


Fig.1-2 Switching Waveforms

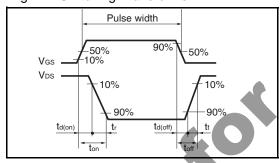


Fig.2-2 Gate Charge Waveform

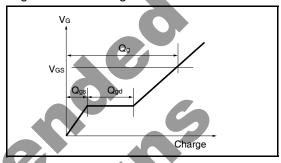


Fig.3-2 Avalanche Waveform

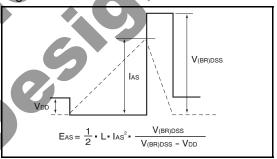


Fig.4-2 dv/dt Waveform

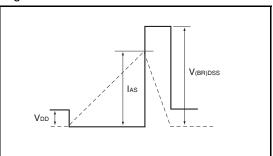
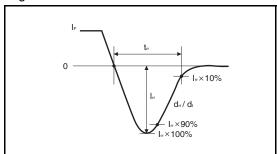
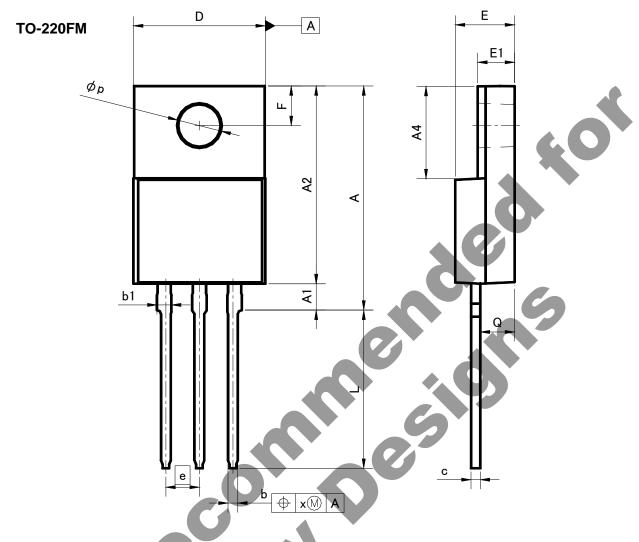


Fig.5-2 di/dt Waveform



●Dimensions (Unit : mm)



DIM	MILIM	MILIMETERS		HES
DIW	MIN	MAX	MIN	MAX
A	16.60	17.60	0.654	0.693
A1	1.80	2.20	0.071	0.087
A2	14.80	15.40	0.583	0.606
A4	6.80	7.20	0.268	0.283
b	0.70	0.85	0.028	0.033
b1	1.10	1.50	0.043	0.059
С	0.70	0.85	0.028	0.033
D	9.90	10.30	0.39	0.406
Е	4.40	4.80	0.173	0.189
е	2.	54	0.	10
E1	2.70	3.00	0.106	0.118
F	2.80	3.20	0.11	0.126
L	11.50	12.50	0.453	0.492
р	3.00	3.40	0.118	0.134
Q	2.10	3.10	0.083	0.122
х	_	0.381	_	0.015

Dimension in mm/inches

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JAPAN	USA	EU	CHINA
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 - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
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- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
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- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

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 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
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- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE2384

NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956

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